

10W 808nm Bare Laser Chip not Bonding on Submount

The 808nm laser chip has the characteristics of low voltage, high efficiency, long life, high reliability and high cost performance. Two different emitter width for choice: 190um and 350um for different application.

The emitter width is 190um, the cavity length is 4mm, conversion efficiency is 60%, and the service lifetime can reach more than 20,000 hours. In addition, the chip also uses a new type of epitaxial structure design and material epitaxy, advanced non-pumped window design and preparation technology, and dry and wet etching combined with self-aligned process technology to control the uniformity of the strip width, especially to ensure mass production. High yield rate, reduce the cost of laser chip. At the same time, the adoption of new technology greatly improves the high temperature resistance characteristics, so that it can work continuously at extremely high temperature.



Data Sheet

Item No: LC808SE10

Item Name: 10W 808nm Single Emitter Laser Chip

Optical

Center Wavelength	808nm
Output Power	10W
Working Mode	CW
Slope Efficiency	1.22W/A
Emitter Width	190um
Emitter Pitch	680um
Cavity length	4nm
Polarization Mode	TE
Slope efficiency	1.22W/A

Electrical

Threshold Current	1.25A
Operating Current	10A
Operating Voltage	1.75V
Power Conversion Efficiency	58%

Thermal

Operating Temperature	15-35°C
Storage Temperature	0-80°C
Wavelength Temp. Coefficient	0.28nm/°C